SCH1430

Power MOSFET 20V, 125mΩ, 2A, Single N-Channel

This low-profile high-power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and ultra low on resistance. This device is suitable for applications with low gate charge driving or ultra low on resistance requirements.

Features

- Low On-Resistance
- 1.8V drive
- ESD Diode-Protected Gate
- Pb-Free, Halogen Free and RoHS compliance
- Ultra small package SCH6 (1.6mm×1.6mm×0.56mmt)

Typical Applications

• Load Switch

SPECIFICATIONS

ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit
Drain to Source Voltage	VDSS	20	V
Gate to Source Voltage	VGSS	±12	V
Drain Current (DC)	ID	2	А
Drain Current (Pulse) PW $\leq 10\mu$ s, duty cycle $\leq 1\%$	IDP	8	А
Power Dissipation When mounted on ceramic substrate $(900 \text{mm}^2 \times 0.8 \text{mm})$	PD	0.8	w
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	–55 to +150	°C

Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate (900mm ² \times 0.8mm)	R _{θJA}	156.2	°C/W

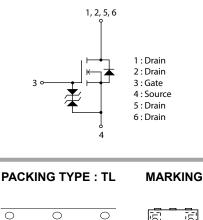


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VDSS	R _{DS} (on) Max	ID Max
20V	125mΩ@ 4.5V	
	190mΩ@ 2.5V	2A
	310mΩ@ 1.8V	

ELECTRICAL CONNECTION N-Channel





ORDERING INFORMATION

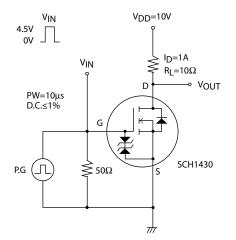
See detailed ordering and shipping information on page 5 of this data sheet.

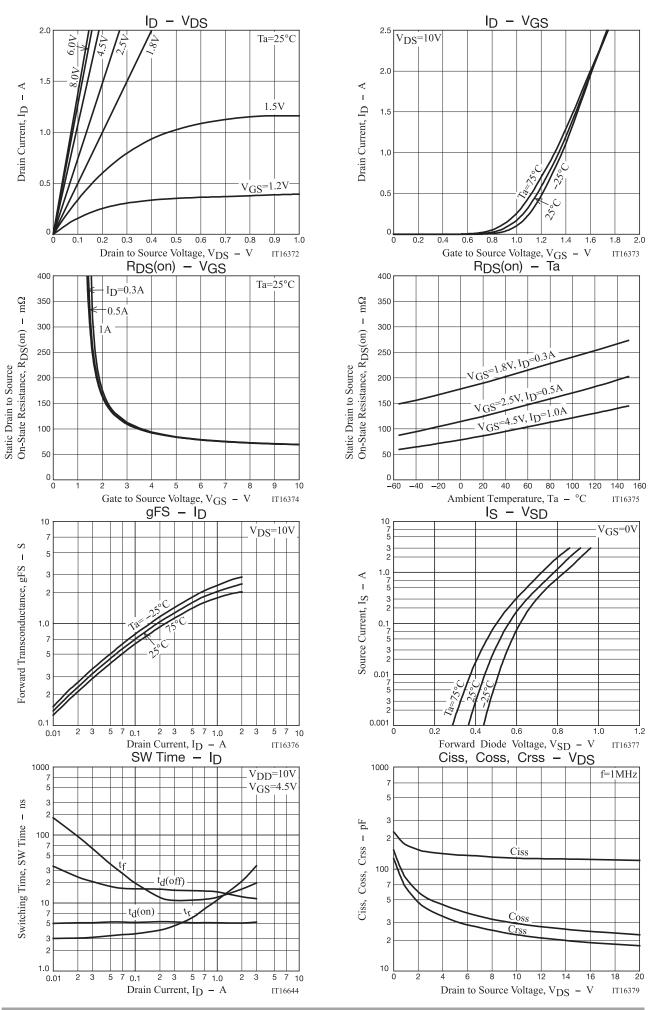
Parameter	Sumbol.	Conditions		Value		
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	20			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =20V, V _{GS} =0V			1	μA
Gate to Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μA
Gate Threshold Voltage	VGS(th)	V _{DS} =10V, I _D =1mA	0.4		1.3	V
Forward Transconductance	9FS	V _{DS} =10V, I _D =1A		1.9		S
Static Drain to Source On-State Resistance	R _{DS} (on)1	ID=1A, VGS=4.5V		93	125	mΩ
	R _{DS} (on)2	ID=0.5A, VGS=2.5V		135	190	mΩ
	R _{DS} (on)3	ID=0.3A, VGS=1.8V		200	310	mΩ
Input Capacitance	Ciss			128		pF
Output Capacitance	Coss	V _{DS} =10V, f=1MHz		28		pF
Reverse Transfer Capacitance	Crss			21		pF
Turn-ON Delay Time	t _d (on)			5.1		ns
Rise Time	tr			11		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit		14.5		ns
Fall Time	tf			12		ns
Total Gate Charge	Qg			1.8		nC
Gate to Source Charge	Qgs	V _{DS} =10V, V _{GS} =4.5V, I _D =2A		0.3		nC
Gate to Drain "Miller" Charge	Qgd			0.55		nC
Forward Diode Voltage	V _{SD}	IS=2A, VGS=0V		0.85	1.2	V

ELECTRICAL CHARACTERISTICS at Ta = 25°C (Note 2)

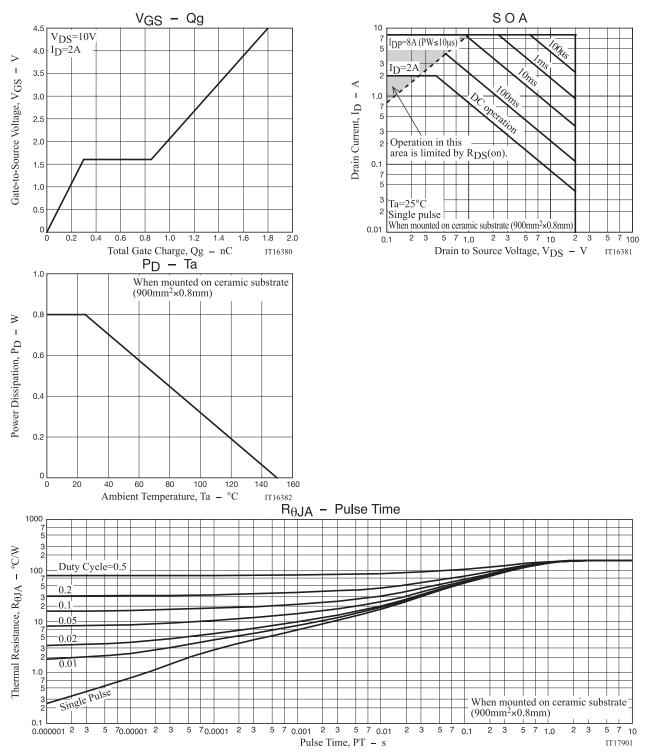
Note 2 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

Switching Time Test Circuit





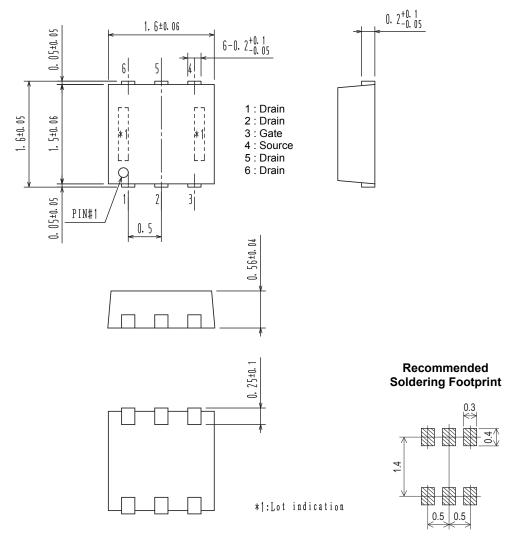
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PACKAGE DIMENSIONS

unit : mm

SOT-563 / SCH6 CASE 463AB ISSUE O



ORDERING INFORMATION

	-			
Device	Marking	Package	Shipping (Qty / Packing)	
SCH1430-TL-H	75	SOT-563 / SCH6	5,000 / Tape & Reel	
SCH1430-TL-W	ZF	(Pb-Free / Halogen Free)		

+ For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

Note on usage : Since the SCH1430 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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